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TRANSMITTAL OF FORMAL DRAWINGS				Docket No. YOR920010499US1 (14710)	
In Re Application Of: Stephen W. Bedell, et al.					
Serial No. 10/055,138	Filing Date January 23, 2002	Confirmation No. 9190	Examiner Stephen J. Stein	Art Unit 1775	
Invention: METHOD OF CREATING HIGH-QUALITY RELAXED SiGe-ON-INSULATOR FOR STRAINED Si CMOS APPLICATION					
Address to: Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450					
Transmitted herewith are:  4 sheets of formal drawing(s) for this application.					
<input checked="" type="checkbox"/> Each sheet of drawing indicates the identifying indicia suggested in 37 CFR Section 1.84(c).					
 Signature			Dated: April 30, 2004		
<div>Steven Fischman Registration No. 34,594  Correspondence Address Customer No. 23389</div>			<div>I certify that this document and attached formal drawings are being deposited on _____ with the U.S. Postal Service as first class mail under 37 C.F.R. 1.8 and addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.</div> <div>Signature of Person Mailing Correspondence</div> <div>Typed or Printed Name of Person Mailing Correspondence</div>		